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Details	
Product Status	Obsolete
Number of LABs/CLBs	1176
Number of Logic Elements/Cells	5292
Total RAM Bits	57344
Number of I/O	140
Number of Gates	200000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc2s200-5pq208i

Spartan-II FPGA Family: Introduction and Ordering Information

DS001-1 (v2.8) June 13, 2008

Product Specification

Introduction

The Spartan®-II Field-Programmable Gate Array family gives users high performance, abundant logic resources, and a rich feature set, all at an exceptionally low price. The six-member family offers densities ranging from 15,000 to 200,000 system gates, as shown in Table 1. System performance is supported up to 200 MHz. Features include block RAM (to 56K bits), distributed RAM (to 75,264 bits), 16 selectable I/O standards, and four DLLs. Fast, predictable interconnect means that successive design iterations continue to meet timing requirements.

The Spartan-II family is a superior alternative to mask-programmed ASICs. The FPGA avoids the initial cost, lengthy development cycles, and inherent risk of conventional ASICs. Also, FPGA programmability permits design upgrades in the field with no hardware replacement necessary (impossible with ASICs).

Features

- Second generation ASIC replacement technology
  - Densities as high as 5,292 logic cells with up to 200,000 system gates
  - Streamlined features based on Virtex® FPGA architecture
  - Unlimited reprogrammability
  - Very low cost
  - Cost-effective 0.18 micron process
- System level features
  - SelectRAM™ hierarchical memory:
    - 16 bits/LUT distributed RAM
    - Configurable 4K bit block RAM
    - Fast interfaces to external RAM
  - Fully PCI compliant
  - Low-power segmented routing architecture
  - Full readback ability for verification/observability
  - Dedicated carry logic for high-speed arithmetic
  - Efficient multiplier support
  - Cascade chain for wide-input functions
  - Abundant registers/latches with enable, set, reset
  - Four dedicated DLLs for advanced clock control
  - Four primary low-skew global clock distribution nets
  - IEEE 1149.1 compatible boundary scan logic
- Versatile I/O and packaging
  - Pb-free package options
  - Low-cost packages available in all densities
  - Family footprint compatibility in common packages
  - 16 high-performance interface standards
  - Hot swap Compact PCI friendly
  - Zero hold time simplifies system timing
- Core logic powered at 2.5V and I/Os powered at 1.5V, 2.5V, or 3.3V
- Fully supported by powerful Xilinx® ISE® development system
  - Fully automatic mapping, placement, and routing

Table 1: **Spartan-II FPGA Family Members**

Device	Logic Cells	System Gates (Logic and RAM)	CLB Array (R x C)	Total CLBs	Maximum Available User I/O(1)	Total Distributed RAM Bits	Total Block RAM Bits
XC2S15	432	15,000	8 x 12	96	86	6,144	16K
XC2S30	972	30,000	12 x 18	216	92	13,824	24K
XC2S50	1,728	50,000	16 x 24	384	176	24,576	32K
XC2S100	2,700	100,000	20 x 30	600	176	38,400	40K
XC2S150	3,888	150,000	24 x 36	864	260	55,296	48K
XC2S200	5,292	200,000	28 x 42	1,176	284	75,264	56K

Notes:
1. All user I/O counts do not include the four global clock/user input pins. See details in Table 2, page 4.

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The three IOB registers function either as edge-triggered D-type flip-flops or as level-sensitive latches. Each IOB has a clock signal (CLK) shared by the three registers and independent Clock Enable (CE) signals for each register. In addition to the CLK and CE control signals, the three registers share a Set/Reset (SR). For each register, this signal can be independently configured as a synchronous Set, a synchronous Reset, an asynchronous Preset, or an asynchronous Clear.

A feature not shown in the block diagram, but controlled by the software, is polarity control. The input and output buffers and all of the IOB control signals have independent polarity controls.

Optional pull-up and pull-down resistors and an optional weak-keeper circuit are attached to each pad. Prior to configuration all outputs not involved in configuration are forced into their high-impedance state. The pull-down resistors and the weak-keeper circuits are inactive, but inputs may optionally be pulled up.

Table 3: **Standards Supported by I/O (Typical Values)**

I/O Standard	Input Reference Voltage (V_{REF})	Output Source Voltage (V_{CCO})	Board Termination Voltage (V_{TT})
LVTTL (2-24 mA)	N/A	3.3	N/A
LVCMOS2	N/A	2.5	N/A
PCI (3V/5V, 33 MHz/66 MHz)	N/A	3.3	N/A
GTL	0.8	N/A	1.2
GTL+	1.0	N/A	1.5
HSTL Class I	0.75	1.5	0.75
HSTL Class III	0.9	1.5	1.5
HSTL Class IV	0.9	1.5	1.5
SSTL3 Class I and II	1.5	3.3	1.5
SSTL2 Class I and II	1.25	2.5	1.25
CTT	1.5	3.3	1.5
AGP-2X	1.32	3.3	N/A

The activation of pull-up resistors prior to configuration is controlled on a global basis by the configuration mode pins. If the pull-up resistors are not activated, all the pins will float. Consequently, external pull-up or pull-down resistors must be provided on pins required to be at a well-defined logic level prior to configuration.

All pads are protected against damage from electrostatic discharge (ESD) and from over-voltage transients. Two forms of over-voltage protection are provided, one that permits 5V compliance, and one that does not. For 5V compliance, a zener-like structure connected to ground turns on when the output rises to approximately 6.5V. When 5V compliance is not required, a conventional clamp diode may be connected to the output supply voltage, V_{CCO}. The type of over-voltage protection can be selected independently for each pad.

All Spartan-II FPGA IOBs support IEEE 1149.1-compatible boundary scan testing.

Input Path

A buffer In the Spartan-II FPGA IOB input path routes the input signal either directly to internal logic or through an optional input flip-flop.

An optional delay element at the D-input of this flip-flop eliminates pad-to-pad hold time. The delay is matched to the internal clock-distribution delay of the FPGA, and when used, assures that the pad-to-pad hold time is zero.

Each input buffer can be configured to conform to any of the low-voltage signaling standards supported. In some of these standards the input buffer utilizes a user-supplied threshold voltage, V_{REF}. The need to supply V_{REF} imposes constraints on which standards can used in close proximity to each other. See "I/O Banking," page 9.

There are optional pull-up and pull-down resistors at each input for use after configuration.

Output Path

The output path includes a 3-state output buffer that drives the output signal onto the pad. The output signal can be routed to the buffer directly from the internal logic or through an optional IOB output flip-flop.

The 3-state control of the output can also be routed directly from the internal logic or through a flip-flip that provides synchronous enable and disable.

Each output driver can be individually programmed for a wide range of low-voltage signaling standards. Each output buffer can source up to 24 mA and sink up to 48 mA. Drive strength and slew rate controls minimize bus transients.

In most signaling standards, the output high voltage depends on an externally supplied V_{CCO} voltage. The need to supply V_{CCO} imposes constraints on which standards can be used in close proximity to each other. See "I/O Banking".

An optional weak-keeper circuit is connected to each output. When selected, the circuit monitors the voltage on the pad and weakly drives the pin High or Low to match the input signal. If the pin is connected to a multiple-source signal, the weak keeper holds the signal in its last state if all

Local Routing

The local routing resources, as shown in Figure 6, provide the following three types of connections:

- Interconnections among the LUTs, flip-flops, and General Routing Matrix (GRM)
- Internal CLB feedback paths that provide high-speed connections to LUTs within the same CLB, chaining them together with minimal routing delay
- Direct paths that provide high-speed connections between horizontally adjacent CLBs, eliminating the delay of the GRM

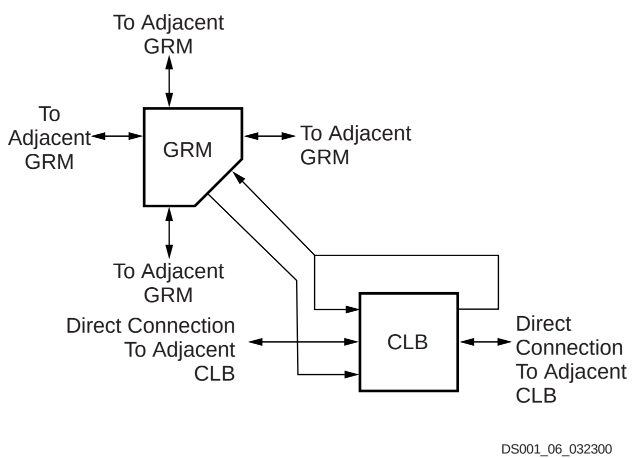


Figure 6: **Spartan-II Local Routing**

General Purpose Routing

Most Spartan-II FPGA signals are routed on the general purpose routing, and consequently, the majority of interconnect resources are associated with this level of the routing hierarchy. The general routing resources are located in horizontal and vertical routing channels associated with the rows and columns CLBs. The general-purpose routing resources are listed below.

- Adjacent to each CLB is a General Routing Matrix (GRM). The GRM is the switch matrix through which horizontal and vertical routing resources connect, and is also the means by which the CLB gains access to the general purpose routing.
- 24 single-length lines route GRM signals to adjacent GRMs in each of the four directions.
- 96 buffered Hex lines route GRM signals to other GRMs six blocks away in each one of the four directions. Organized in a staggered pattern, Hex lines may be driven only at their endpoints. Hex-line signals can be accessed either at the endpoints or at the midpoint (three blocks from the source). One third of the Hex lines are bidirectional, while the remaining ones are unidirectional.
- 12 Longlines are buffered, bidirectional wires that distribute signals across the device quickly and efficiently. Vertical Longlines span the full height of the device, and horizontal ones span the full width of the device.

I/O Routing

Spartan-II devices have additional routing resources around their periphery that form an interface between the CLB array and the IOBs. This additional routing, called the VersaRing, facilitates pin-swapping and pin-locking, such that logic redesigns can adapt to existing PCB layouts. Time-to-market is reduced, since PCBs and other system components can be manufactured while the logic design is still in progress.

Dedicated Routing

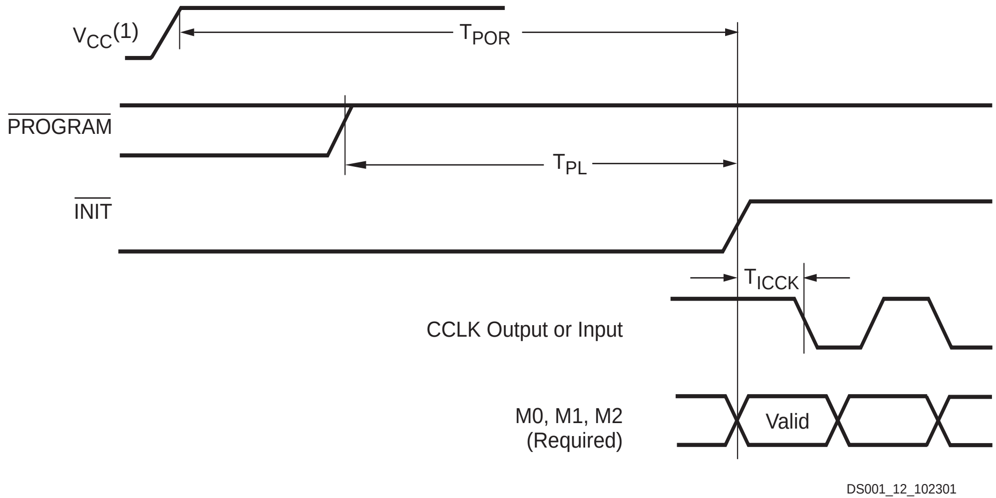
Some classes of signal require dedicated routing resources to maximize performance. In the Spartan-II architecture, dedicated routing resources are provided for two classes of signal.

- Horizontal routing resources are provided for on-chip 3-state busses. Four partitionable bus lines are provided per CLB row, permitting multiple busses within a row, as shown in Figure 7.
- Two dedicated nets per CLB propagate carry signals vertically to the adjacent CLB.

Global Routing

Global Routing resources distribute clocks and other signals with very high fanout throughout the device. Spartan-II devices include two tiers of global routing resources referred to as primary and secondary global routing resources.

- The primary global routing resources are four dedicated global nets with dedicated input pins that are designed to distribute high-fanout clock signals with minimal skew. Each global clock net can drive all CLB, IOB, and block RAM clock pins. The primary global nets may only be driven by global buffers. There are four global buffers, one for each global net.
- The secondary global routing resources consist of 24 backbone lines, 12 across the top of the chip and 12 across bottom. From these lines, up to 12 unique signals per column can be distributed via the 12 longlines in the column. These secondary resources are more flexible than the primary resources since they are not restricted to routing only to clock pins.



Symbol	Description	Min	Max
T_{POR}	Power-on reset	-	2 ms
T_{PL}	Program latency	-	100 µs
T_{ICCK}	CCLK output delay (Master Serial mode only)	0.5 µs	4 µs
$T_{PROGRAM}$	Program pulse width	300 ns	-

Notes: (referring to waveform above:)
1. Before configuration can begin, V_{CCINT} must be greater than 1.6V and V_{CCO} Bank 2 must be greater than 1.0V.

Figure 12: **Configuration Timing on Power-Up**

Clearing Configuration Memory

The device indicates that clearing the configuration memory is in progress by driving INIT Low. At this time, the user can delay configuration by holding either PROGRAM or INIT Low, which causes the device to remain in the memory clearing phase. Note that the bidirectional INIT line is driving a Low logic level during memory clearing. To avoid contention, use an open-drain driver to keep INIT Low.

With no delay in force, the device indicates that the memory is completely clear by driving INIT High. The FPGA samples its mode pins on this Low-to-High transition.

Loading Configuration Data

Once INIT is High, the user can begin loading configuration data frames into the device. The details of loading the configuration data are discussed in the sections treating the configuration modes individually. The sequence of operations necessary to load configuration data using the serial modes is shown in Figure 14. Loading data using the Slave Parallel mode is shown in Figure 19, page 25.

CRC Error Checking

During the loading of configuration data, a CRC value embedded in the configuration file is checked against a CRC value calculated within the FPGA. If the CRC values do not match, the FPGA drives INIT Low to indicate that a frame error has occurred and configuration is aborted.

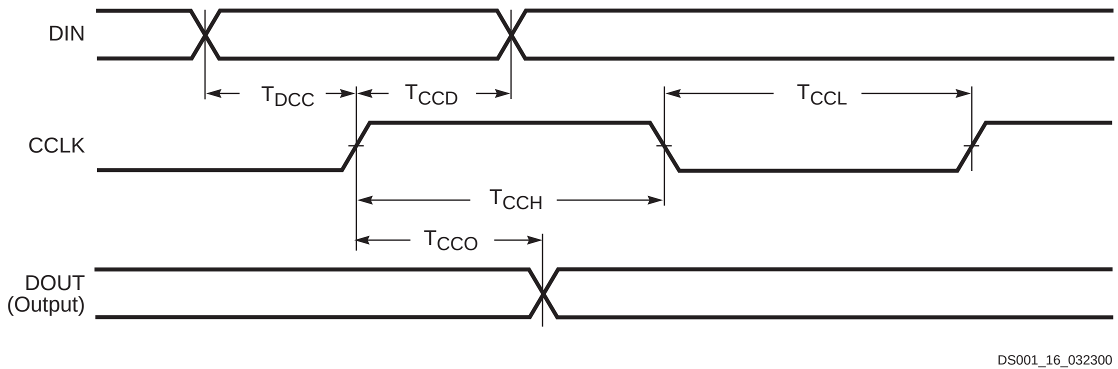
To reconfigure the device, the PROGRAM pin should be asserted to reset the configuration logic. Recycling power also resets the FPGA for configuration. See "Clearing Configuration Memory".

Start-up

The start-up sequence oversees the transition of the FPGA from the configuration state to full user operation. A match of CRC values, indicating a successful loading of the configuration data, initiates the sequence.

During start-up, the device performs four operations:

1. The assertion of DONE. The failure of DONE to go High may indicate the unsuccessful loading of configuration data.
2. The release of the Global Three State net. This activates I/Os to which signals are assigned. The remaining I/Os stay in a high-impedance state with internal weak pull-down resistors present.
3. Negates Global Set Reset (GSR). This allows all flip-flops to change state.
4. The assertion of Global Write Enable (GWE). This allows all RAMs and flip-flops to change state.



Symbol		Description		Units
T_{DCC}	CCLK	DIN setup	5	ns, min
T_{CCD}		DIN hold	0	ns, min
T_{CCO}		DOUT	12	ns, max
T_{CCH}		High time	5	ns, min
T_{CCL}		Low time	5	ns, min
F_{CC}		Maximum frequency	66	MHz, max

Figure 16: **Slave Serial Mode Timing**

If CCLK is slower than F_{CCNH}, the FPGA will never assert BUSY. In this case, the above handshake is unnecessary, and data can simply be entered into the FPGA every CCLK cycle.

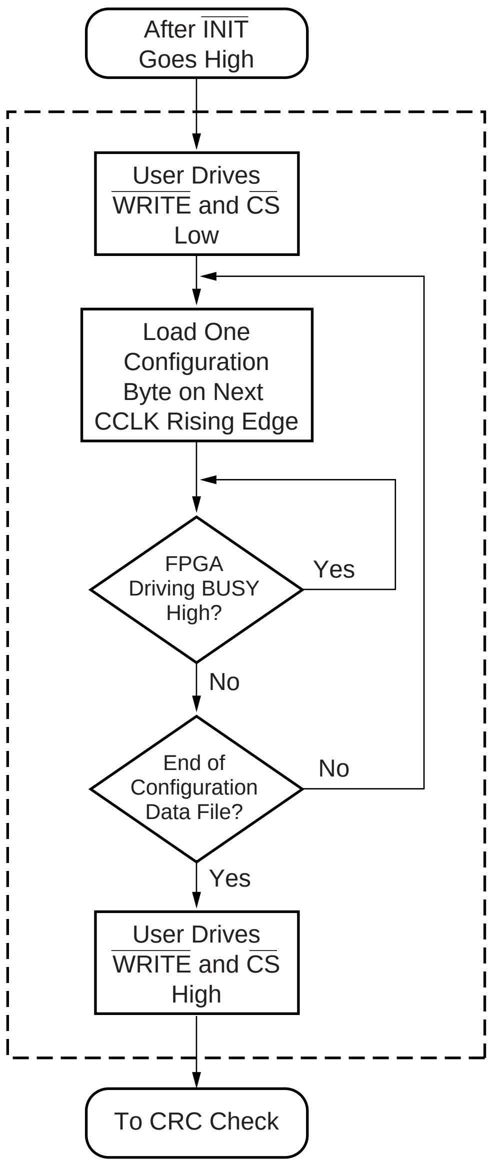


Figure 19: **Loading Configuration Data for the Slave Parallel Mode**

A configuration packet does not have to be written in one continuous stretch, rather it can be split into many write sequences. Each sequence would involve assertion of CS.

In applications where multiple clock cycles may be required to access the configuration data before each byte can be loaded into the Slave Parallel interface, a new byte of data may not be ready for each consecutive CCLK edge. In such a case the CS signal may be de-asserted until the next byte is valid on D0-D7. While CS is High, the Slave Parallel interface does not expect any data and ignores all CCLK transitions. However, to avoid aborting configuration, WRITE must continue to be asserted while CS is asserted.

Abort

To abort configuration during a write sequence, de-assert WRITE while holding CS Low. The abort operation is initiated at the rising edge of CCLK, as shown in Figure 21, page 26. The device will remain BUSY until the aborted operation is complete. After aborting configuration, data is assumed to be unaligned to word boundaries and the FPGA requires a new synchronization word prior to accepting any new packets.

Boundary-Scan Mode

In the boundary-scan mode, no nondedicated pins are required, configuration being done entirely through the IEEE 1149.1 Test Access Port.

Configuration through the TAP uses the special CFG_IN instruction. This instruction allows data input on TDI to be converted into data packets for the internal configuration bus.

The following steps are required to configure the FPGA through the boundary-scan port.

1. Load the CFG_IN instruction into the boundary-scan instruction register (IR)
2. Enter the Shift-DR (SDR) state
3. Shift a standard configuration bitstream into TDI
4. Return to Run-Test-Idle (RTI)
5. Load the JSTART instruction into IR
6. Enter the SDR state
7. Clock TCK through the sequence (the length is programmable)
8. Return to RTI

Configuration and readback via the TAP is always available. The boundary-scan mode simply locks out the other modes. The boundary-scan mode is selected by a <10x> on the mode pins (M0, M1, M2).

Readback

The configuration data stored in the Spartan-II FPGA configuration memory can be readback for verification. Along with the configuration data it is possible to readback the contents of all flip-flops/latches, LUT RAMs, and block RAMs. This capability is used for real-time debugging.

For more detailed information see XAPP176, *Spartan-II FPGA Family Configuration and Readback.*

Using Block RAM Features

The Spartan-II FPGA family provides dedicated blocks of on-chip, true dual-read/write port synchronous RAM, with 4096 memory cells. Each port of the block RAM memory can be independently configured as a read/write port, a read port, a write port, and can be configured to a specific data width. The block RAM memory offers new capabilities allowing the FPGA designer to simplify designs.

Operating Modes

Block RAM memory supports two operating modes.

- Read Through
- Write Back

Read Through (One Clock Edge)

The read address is registered on the read port clock edge and data appears on the output after the RAM access time. Some memories may place the latch/register at the outputs depending on the desire to have a faster clock-to-out versus setup time. This is generally considered to be an inferior solution since it changes the read operation to an asynchronous function with the possibility of missing an address/control line transition during the generation of the read pulse clock.

Write Back (One Clock Edge)

The write address is registered on the write port clock edge and the data input is written to the memory and mirrored on the write port input.

Block RAM Characteristics

1. All inputs are registered with the port clock and have a setup to clock timing specification.
2. All outputs have a read through or write back function depending on the state of the port WE pin. The outputs relative to the port clock are available after the clock-to-out timing specification.
3. The block RAM are true SRAM memories and do not have a combinatorial path from the address to the output. The LUT cells in the CLBs are still available with this function.
4. The ports are completely independent from each other (*i.e.,* clocking, control, address, read/write function, and data width) without arbitration.
5. A write operation requires only one clock edge.
6. A read operation requires only one clock edge.

The output ports are latched with a self timed circuit to guarantee a glitch free read. The state of the output port will not change until the port executes another read or write operation.

Library Primitives

Figure 31 and Figure 32 show the two generic library block RAM primitives. Table 11 describes all of the available primitives for synthesis and simulation.

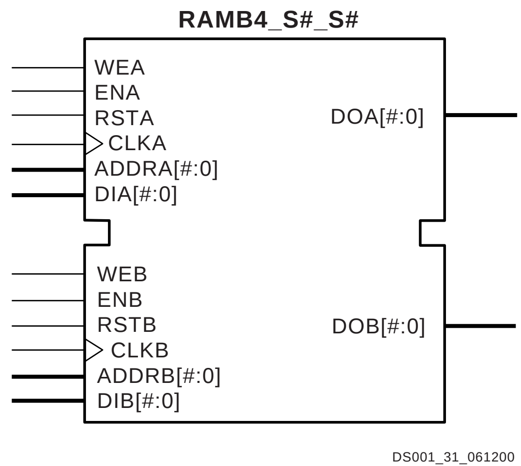


Figure 31: **Dual-Port Block RAM Memory**

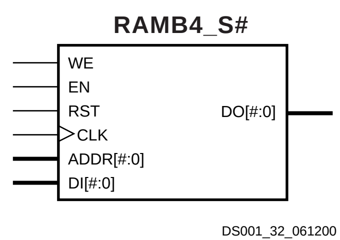


Figure 32: **Single-Port Block RAM Memory**

Table 11: **Available Library Primitives**

Primitive	Port A Width	Port B Width
RAMB4_S1	1	N/A
RAMB4_S1_S1		1
RAMB4_S1_S2		2
RAMB4_S1_S4		4
RAMB4_S1_S8		8
RAMB4_S1_S16		16
RAMB4_S2	2	N/A
RAMB4_S2_S2		2
RAMB4_S2_S4		4
RAMB4_S2_S8		8
RAMB4_S2_S16		16

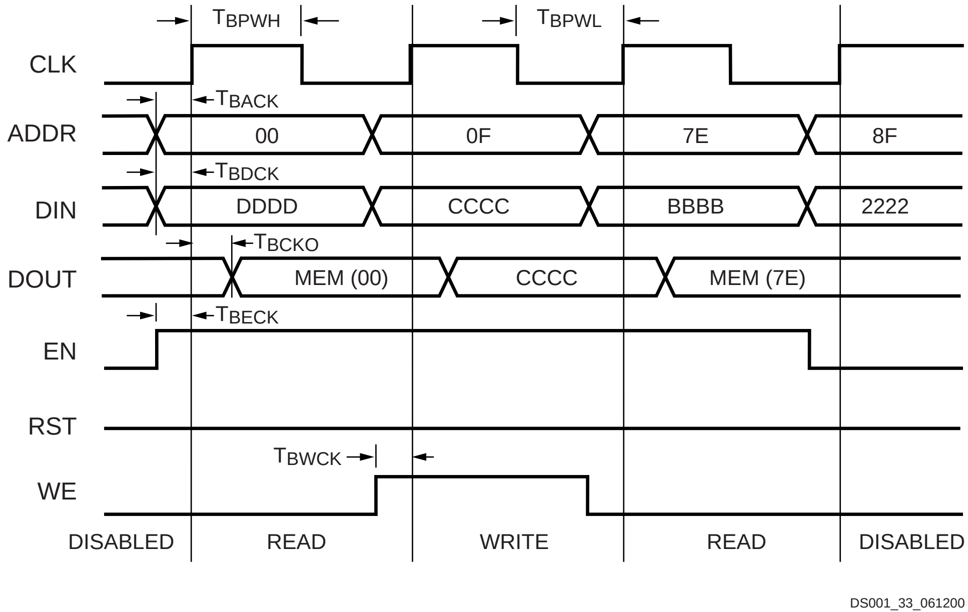


Figure 33: **Timing Diagram for Single-Port Block RAM Memory**

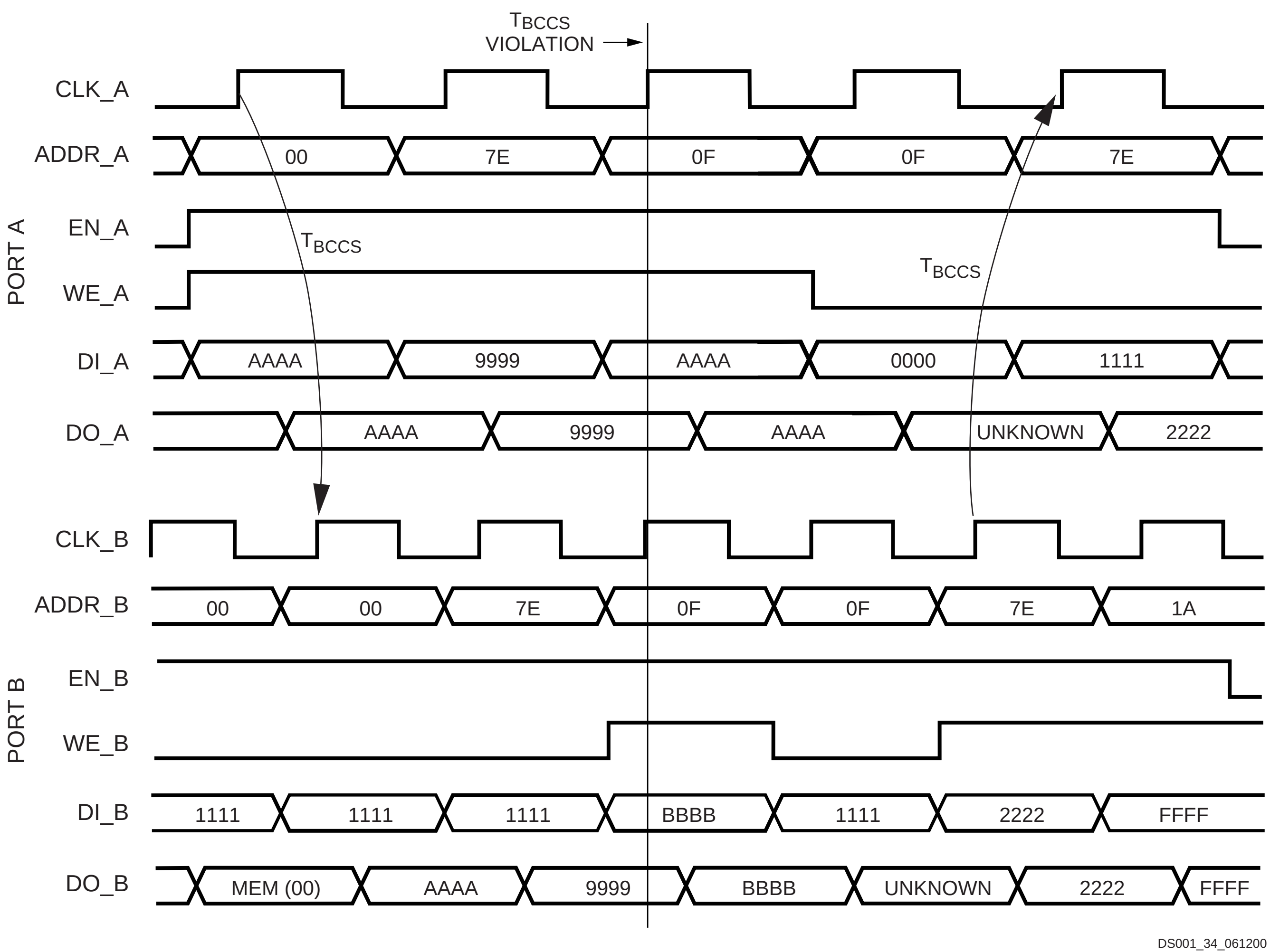


Figure 34: **Timing Diagram for a True Dual-Port Read/Write Block RAM Memory**

LVTTL

LVTTL requires no termination. DC voltage specifications appears in Table 32 for the LVTTL standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Table 32: **LVTTL Voltage Specifications**

Parameter	Min	Typ	Max
V_{CCO}	3.0	3.3	3.6
V_{REF}	-	-	-
V_{TT}	-	-	-
V_{IH}	2.0	-	5.5
V_{IL}	–0.5	-	0.8
V_{OH}	2.4	-	-
V_{OL}	-	-	0.4
I_{OH} at V_{OH} (mA)	–24	-	-
I_{OL} at V_{OL} (mA)	24	-	-

Notes:
1. V_{OL} and V_{OH} for lower drive currents sample tested.

LVCMOS2

LVCMOS2 requires no termination. DC voltage specifications appear in Table 33 for the LVCMOS2 standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Table 33: **LVCMOS2 Voltage Specifications**

Parameter	Min	Typ	Max
V_{CCO}	2.3	2.5	2.7
V_{REF}	-	-	-
V_{TT}	-	-	-
V_{IH}	1.7	-	5.5
V_{IL}	–0.5	-	0.7
V_{OH}	1.9	-	-
V_{OL}	-	-	0.4
I_{OH} at V_{OH} (mA)	–12	-	-
I_{OL} at V_{OL} (mA)	12	-	-

AGP-2X

The specification for the AGP-2X standard does not document a recommended termination technique. DC voltage specifications appear in Table 34 for the AGP-2X standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Table 34: **AGP-2X Voltage Specifications**

Parameter	Min	Typ	Max
V_{CCO}	3.0	3.3	3.6
$V_{REF} = N \times V_{CCO}$(1)	1.17	1.32	1.48
V_{TT}	-	-	-
$V_{IH} \geq V_{REF} + 0.2$	1.37	1.52	-
$V_{IL} \leq V_{REF} - 0.2$	-	1.12	1.28
$V_{OH} \geq 0.9 \times V_{CCO}$	2.7	3.0	-
$V_{OL} \leq 0.1 \times V_{CCO}$	-	0.33	0.36
I_{OH} at V_{OH} (mA)	Note 2	-	-
I_{OL} at V_{OL} (mA)	Note 2	-	-

Notes:
1. N must be greater than or equal to 0.39 and less than or equal to 0.41.
2. Tested according to the relevant specification.

For design examples and more information on using the I/O, see XAPP179, *Using SelectIO Interfaces in Spartan-II and Spartan-IIE FPGAs*.

Definition of Terms

In this document, some specifications may be designated as Advance or Preliminary. These terms are defined as follows:

Advance: Initial estimates based on simulation and/or extrapolation from other speed grades, devices, or families. Values are subject to change. Use as estimates, not for production.

Preliminary: Based on preliminary characterization. Further changes are not expected.

Unmarked: Specifications not identified as either Advance or Preliminary are to be considered Final.

Except for pin-to-pin input and output parameters, the AC parameter delay specifications included in this document are derived from measuring internal test patterns. All limits are representative of worst-case supply voltage and junction temperature conditions. Typical numbers are based on measurements taken at a nominal V_{CCINT} level of 2.5V and a junction temperature of 25°C. The parameters included are common to popular designs and typical applications. **All specifications are subject to change without notice.**

DC Specifications

Absolute Maximum Ratings(1)

Symbol	Description		Min	Max	Units
V_{CCINT}	Supply voltage relative to GND(2)		–0.5	3.0	V
V_{CCO}	Supply voltage relative to GND(2)		–0.5	4.0	V
V_{REF}	Input reference voltage		–0.5	3.6	V
V_{IN}	Input voltage relative to GND(3)	5V tolerant I/O(4)	–0.5	5.5	V
		No 5V tolerance(5)	–0.5	V_{CCO} + 0.5	V
V_{TS}	Voltage applied to 3-state output	5V tolerant I/O(4)	–0.5	5.5	V
		No 5V tolerance(5)	–0.5	V_{CCO} + 0.5	V
T_{STG}	Storage temperature (ambient)		–65	+150	°C
T_J	Junction temperature		-	+125	°C

Notes:
1. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time may affect device reliability.
2. Power supplies may turn on in any order.
3. V_{IN} should not exceed V_{CCO} by more than 3.6V over extended periods of time (e.g., longer than a day).
4. Spartan®-II device I/Os are 5V Tolerant whenever the LVTTL, LVCMOS2, or PCI33_5 signal standard has been selected. With 5V Tolerant I/Os selected, the Maximum DC overshoot must be limited to either +5.5V or 10 mA, and undershoot must be limited to either –0.5V or 10 mA, whichever is easier to achieve. The Maximum AC conditions are as follows: The device pins may undershoot to –2.0V or overshoot to +7.0V, provided this over/undershoot lasts no more than 11 ns with a forcing current no greater than 100 mA.
5. Without 5V Tolerant I/Os selected, the Maximum DC overshoot must be limited to either V_{CCO} + 0.5V or 10 mA, and undershoot must be limited to –0.5V or 10 mA, whichever is easier to achieve. The Maximum AC conditions are as follows: The device pins may undershoot to –2.0V or overshoot to V_{CCO} + 2.0V, provided this over/undershoot lasts no more than 11 ns with a forcing current no greater than 100 mA.
6. For soldering guidelines, see the Packaging Information on the Xilinx® web site.

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Input/Output Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
CTT	–0.5	V_{REF} – 0.2	V_{REF} + 0.2	3.6	V_{REF} – 0.4	V_{REF} + 0.4	8	–8
AGP	–0.5	V_{REF} – 0.2	V_{REF} + 0.2	3.6	10% V_{CCO}	90% V_{CCO}	Note (2)	Note (2)

Notes:
1. V_{OL} and V_{OH} for lower drive currents are sample tested.
2. Tested according to the relevant specifications.

Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values. For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer (TRCE in the Xilinx Development System) and back-annotated to the simulation netlist. All timing parameters assume worst-case operating conditions (supply voltage and junction temperature). Values apply to all Spartan-II devices unless otherwise noted.

Global Clock Input to Output Delay for LVTTL, *with* DLL (Pin-to-Pin)(1)

Symbol	Description	Device	Speed Grade			Units
			All	-6	-5	
			Min	Max	Max	
$T_{ICKOFDLL}$	Global clock input to output delay using output flip-flop for LVTTL, 12 mA, fast slew rate, *with* DLL.	All		2.9	3.3	ns

Notes:
1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. The 35 pF load does not apply to the Min values. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.
3. DLL output jitter is already included in the timing calculation.
4. For data *output* with different standards, adjust delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59. For a global clock input with standards other than LVTTL, adjust delays with values from the "I/O Standard Global Clock Input Adjustments," page 61.

Global Clock Input to Output Delay for LVTTL, *without* DLL (Pin-to-Pin)(1)

Symbol	Description	Device	Speed Grade			Units
			All	-6	-5	
			Min	Max	Max	
T_{ICKOF}	Global clock input to output delay using output flip-flop for LVTTL, 12 mA, fast slew rate, *without* DLL.	XC2S15		4.5	5.4	ns
		XC2S30		4.5	5.4	ns
		XC2S50		4.5	5.4	ns
		XC2S100		4.6	5.5	ns
		XC2S150		4.6	5.5	ns
		XC2S200		4.7	5.6	ns

Notes:
1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. The 35 pF load does not apply to the Min values. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.
3. For data *output* with different standards, adjust delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59. For a global clock input with standards other than LVTTL, adjust delays with values from the "I/O Standard Global Clock Input Adjustments," page 61.

IOB Input Switching Characteristics[1]

Input delays associated with the pad are specified for LVTTL levels. For other standards, adjust the delays with the values shown in "IOB Input Delay Adjustments for Different Standards," page 57.

Symbol	Description	Device	Speed Grade -6 Min	Speed Grade -6 Max	Speed Grade -5 Min	Speed Grade -5 Max	Units
Propagation Delays							
T_{IOPI}	Pad to I output, no delay	All	-	0.8	-	1.0	ns
T_{IOPID}	Pad to I output, with delay	All	-	1.5	-	1.8	ns
T_{IOPLI}	Pad to output IQ via transparent latch, no delay	All	-	1.7	-	2.0	ns
T_{IOPLID}	Pad to output IQ via transparent latch, with delay	XC2S15	-	3.8	-	4.5	ns
		XC2S30	-	3.8	-	4.5	ns
		XC2S50	-	3.8	-	4.5	ns
		XC2S100	-	3.8	-	4.5	ns
		XC2S150	-	4.0	-	4.7	ns
		XC2S200	-	4.0	-	4.7	ns
Sequential Delays							
T_{IOCKIQ}	Clock CLK to output IQ	All	-	0.7	-	0.8	ns
Setup/Hold Times with Respect to Clock CLK[2]							
T_{IOPICK} / T_{IOICKP}	Pad, no delay	All	1.7 / 0	-	1.9 / 0	-	ns
$T_{IOPICKD}$ / $T_{IOICKPD}$	Pad, with delay[1]	XC2S15	3.8 / 0	-	4.4 / 0	-	ns
		XC2S30	3.8 / 0	-	4.4 / 0	-	ns
		XC2S50	3.8 / 0	-	4.4 / 0	-	ns
		XC2S100	3.8 / 0	-	4.4 / 0	-	ns
		XC2S150	3.9 / 0	-	4.6 / 0	-	ns
		XC2S200	3.9 / 0	-	4.6 / 0	-	ns
$T_{IOICECK}$ / $T_{IOCKICE}$	ICE input	All	0.9 / 0.01	-	0.9 / 0.01	-	ns
Set/Reset Delays							
$T_{IOSRCKI}$	SR input (IFF, synchronous)	All	-	1.1	-	1.2	ns
T_{IOSRIQ}	SR input to IQ (asynchronous)	All	-	1.5	-	1.7	ns
T_{GSRQ}	GSR to output IQ	All	-	9.9	-	11.7	ns

Notes:
1. Input timing for LVTTL is measured at 1.4V. For other I/O standards, see the table "Delay Measurement Methodology," page 60.
2. A zero hold time listing indicates no hold time or a negative hold time.

IOB Output Delay Adjustments for Different Standards(1)

Output delays terminating at a pad are specified for LVTTL with 12 mA drive and fast slew rate. For other standards, adjust the delays by the values shown. A delay adjusted in this way constitutes a worst-case limit.

Symbol	Description	Standard	Speed Grade -6	Speed Grade -5	Units
Output Delay Adjustments (Adj)					
T_{OLVTTL_S2}	Standard-specific adjustments for output delays terminating at pads (based on standard capacitive load, C_{SL})	LVTTL, Slow, 2 mA	14.2	16.9	ns
T_{OLVTTL_S4}		4 mA	7.2	8.6	ns
T_{OLVTTL_S6}		6 mA	4.7	5.5	ns
T_{OLVTTL_S8}		8 mA	2.9	3.5	ns
T_{OLVTTL_S12}		12 mA	1.9	2.2	ns
T_{OLVTTL_S16}		16 mA	1.7	2.0	ns
T_{OLVTTL_S24}		24 mA	1.3	1.5	ns
T_{OLVTTL_F2}		LVTTL, Fast, 2 mA	12.6	15.0	ns
T_{OLVTTL_F4}		4 mA	5.1	6.1	ns
T_{OLVTTL_F6}		6 mA	3.0	3.6	ns
T_{OLVTTL_F8}		8 mA	1.0	1.2	ns
T_{OLVTTL_F12}		12 mA	0	0	ns
T_{OLVTTL_F16}		16 mA	–0.1	–0.1	ns
T_{OLVTTL_F24}		24 mA	–0.1	–0.2	ns
$T_{OLVCMOS2}$		LVCMOS2	0.2	0.2	ns
T_{OPCI33_3}		PCI, 33 MHz, 3.3V	2.4	2.9	ns
T_{OPCI33_5}		PCI, 33 MHz, 5.0V	2.9	3.5	ns
T_{OPCI66_3}		PCI, 66 MHz, 3.3V	–0.3	–0.4	ns
T_{OGTL}		GTL	0.6	0.7	ns
T_{OGTLP}		GTL+	0.9	1.1	ns
T_{OHSTL_I}		HSTL I	–0.4	–0.5	ns
T_{OHSTL_III}		HSTL III	–0.8	–1.0	ns
T_{OHSTL_IV}		HSTL IV	–0.9	–1.1	ns
T_{OSSTL2_I}		SSTL2 I	–0.4	–0.5	ns
T_{OSSLT2_II}		SSTL2 II	–0.8	–1.0	ns
T_{OSSTL3_I}		SSTL3 I	–0.4	–0.5	ns
T_{OSSTL3_II}		SSTL3 II	–0.9	–1.1	ns
T_{OCTT}		CTT	–0.5	–0.6	ns
T_{OAGP}		AGP	–0.8	–1.0	ns

Notes:
1. Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.

CLB Arithmetic Switching Characteristics

Setup times not listed explicitly can be approximated by decreasing the combinatorial delays by the setup time adjustment listed. Precise values are provided by the timing analyzer.

Symbol	Description	Speed Grade				Units
		-6		-5		
		Min	Max	Min	Max	
Combinatorial Delays						
T_{OPX}	F operand inputs to X via XOR	-	0.8	-	0.9	ns
T_{OPXB}	F operand input to XB output	-	1.3	-	1.5	ns
T_{OPY}	F operand input to Y via XOR	-	1.7	-	2.0	ns
T_{OPYB}	F operand input to YB output	-	1.7	-	2.0	ns
T_{OPCYF}	F operand input to COUT output	-	1.3	-	1.5	ns
T_{OPGY}	G operand inputs to Y via XOR	-	0.9	-	1.1	ns
T_{OPGYB}	G operand input to YB output	-	1.6	-	2.0	ns
T_{OPCYG}	G operand input to COUT output	-	1.2	-	1.4	ns
T_{BXCY}	BX initialization input to COUT	-	0.9	-	1.0	ns
T_{CINX}	CIN input to X output via XOR	-	0.4	-	0.5	ns
T_{CINXB}	CIN input to XB	-	0.1	-	0.1	ns
T_{CINY}	CIN input to Y via XOR	-	0.5	-	0.6	ns
T_{CINYB}	CIN input to YB	-	0.6	-	0.7	ns
T_{BYP}	CIN input to COUT output	-	0.1	-	0.1	ns
Multiplier Operation						
T_{FANDXB}	F1/2 operand inputs to XB output via AND	-	0.5	-	0.5	ns
T_{FANDYB}	F1/2 operand inputs to YB output via AND	-	0.9	-	1.1	ns
T_{FANDCY}	F1/2 operand inputs to COUT output via AND	-	0.5	-	0.6	ns
T_{GANDYB}	G1/2 operand inputs to YB output via AND	-	0.6	-	0.7	ns
T_{GANDCY}	G1/2 operand inputs to COUT output via AND	-	0.2	-	0.2	ns
Setup/Hold Times with Respect to Clock CLK(1)						
T_{CCKX} / T_{CKCX}	CIN input to FFX	1.1 / 0	-	1.2 / 0	-	ns
T_{CCKY} / T_{CKCY}	CIN input to FFY	1.2 / 0	-	1.3 / 0	-	ns

Notes:
1. A zero hold time listing indicates no hold time or a negative hold time.

Table 36: **Spartan-II Family Package Options**

Package	Leads	Type	Maximum I/O	Lead Pitch (mm)	Footprint Area (mm)	Height (mm)	Mass[(1)] (g)
VQ100 / VQG100	100	Very Thin Quad Flat Pack (VQFP)	60	0.5	16 x 16	1.20	0.6
TQ144 / TQG144	144	Thin Quad Flat Pack (TQFP)	92	0.5	22 x 22	1.60	1.4
CS144 / CSG144	144	Chip Scale Ball Grid Array (CSBGA)	92	0.8	12 x 12	1.20	0.3
PQ208 / PQG208	208	Plastic Quad Flat Pack (PQFP)	140	0.5	30.6 x 30.6	3.70	5.3
FG256 / FGG256	256	Fine-pitch Ball Grid Array (FBGA)	176	1.0	17 x 17	2.00	0.9
FG456 / FGG456	456	Fine-pitch Ball Grid Array (FBGA)	284	1.0	23 x 23	2.60	2.2

Notes:

1. Package mass is ±10%.

Note: Some early versions of Spartan-II devices, including the XC2S15 and XC2S30 ES devices and the XC2S150 with date code 0045 or earlier, included a power-down pin. For more information, see Answer Record 10500.

VCCO Banks

Some of the I/O standards require specific V_{CCO} voltages. These voltages are externally connected to device pins that serve groups of IOBs, called banks. Eight I/O banks result from separating each edge of the FPGA into two banks (see Figure 3 in Module 2). Each bank has multiple V_{CCO} pins which must be connected to the same voltage. In the smaller packages, the V_{CCO} pins are connected between banks, effectively reducing the number of independent banks available (see Table 37). These interconnected banks are shown in the Pinout Tables with V_{CCO} pads for multiple banks connected to the same pin.

Table 37: **Independent VCCO Banks Available**

Package	VQ100 PQ208	CS144 TQ144	FG256 FG456
Independent Banks	1	4	8

Package Overview

Table 36 shows the six low-cost, space-saving production package styles for the Spartan-II family.

Each package style is available in an environmentally friendly lead-free (Pb-free) option. The Pb-free packages include an extra 'G' in the package style name. For example, the standard "CS144" package becomes "CSG144" when ordered as the Pb-free option. Leaded (non-Pb-free) packages may be available for selected devices, with the same pin-out and without the "G" in the ordering code; contact Xilinx sales for more information. The mechanical dimensions of the standard and Pb-free packages are similar, as shown in the mechanical drawings provided in Table 38.

For additional package information, see UG112: *Device Package User Guide*.

Mechanical Drawings

Detailed mechanical drawings for each package type are available from the Xilinx web site at the specified location in Table 38.

Material Declaration Data Sheets (MDDS) are also available on the Xilinx web site for each package.

Table 38: **Xilinx Package Documentation**

Package	Drawing	MDDS
VQ100	Package Drawing	PK173_VQ100
VQG100		PK130_VQG100
TQ144	Package Drawing	PK169_TQ144
TQG144		PK126_TQG144
CS144	Package Drawing	PK149_CS144
CSG144		PK103_CSG144
PQ208	Package Drawing	PK166_PQ208
PQG208		PK123_PQG208
FG256	Package Drawing	PK151_FG256
FGG256		PK105_FGG256
FG456	Package Drawing	PK154_FG456
FGG456		PK109_FGG456

Pinout Tables

The following device-specific pinout tables include all packages available for each Spartan®-II device. They follow the pad locations around the die, and include Boundary Scan register locations.

XC2S15 Device Pinouts

XC2S15 Pad Name					
Function	Bank	VQ100	TQ144	CS144	Bndry Scan
GND	-	P1	P143	A1	-
TMS	-	P2	P142	B1	-
I/O	7	P3	P141	C2	77
I/O	7	-	P140	C1	80
I/O, V_{REF}	7	P4	P139	D4	83
I/O	7	P5	P137	D2	86
I/O	7	P6	P136	D1	89
GND	-	-	P135	E4	-
I/O	7	P7	P134	E3	92
I/O	7	-	P133	E2	95
I/O, V_{REF}	7	P8	P132	E1	98
I/O	7	P9	P131	F4	101
I/O	7	-	P130	F3	104
I/O, IRDY(1)	7	P10	P129	F2	107
GND	-	P11	P128	F1	-
V_{CCO}	7	P12	P127	G2	-
V_{CCO}	6	P12	P127	G2	-
I/O, TRDY(1)	6	P13	P126	G1	110
V_{CCINT}	-	P14	P125	G3	-
I/O	6	-	P124	G4	113
I/O	6	P15	P123	H1	116
I/O, V_{REF}	6	P16	P122	H2	119
I/O	6	-	P121	H3	122
I/O	6	P17	P120	H4	125
GND	-	-	P119	J1	-
I/O	6	P18	P118	J2	128
I/O	6	P19	P117	J3	131
I/O, V_{REF}	6	P20	P115	K1	134
I/O	6	-	P114	K2	137
I/O	6	P21	P113	K3	140
I/O	6	P22	P112	L1	143
M1	-	P23	P111	L2	146
GND	-	P24	P110	L3	-
M0	-	P25	P109	M1	147
V_{CCO}	6	P26	P108	M2	-
V_{CCO}	5	P26	P107	N1	-

XC2S15 Device Pinouts *(Continued)*

XC2S15 Pad Name					
Function	Bank	VQ100	TQ144	CS144	Bndry Scan
M2	-	P27	P106	N2	148
I/O	5	-	P103	K4	155
I/O, V_{REF}	5	P30	P102	L4	158
I/O	5	P31	P100	N4	161
I/O	5	P32	P99	K5	164
GND	-	-	P98	L5	-
V_{CCINT}	-	P33	P97	M5	-
I/O	5	-	P96	N5	167
I/O	5	-	P95	K6	170
I/O, V_{REF}	5	P34	P94	L6	173
I/O	5	-	P93	M6	176
V_{CCINT}	-	P35	P92	N6	-
I, GCK1	5	P36	P91	M7	185
V_{CCO}	5	P37	P90	N7	-
V_{CCO}	4	P37	P90	N7	-
GND	-	P38	P89	L7	-
I, GCK0	4	P39	P88	K7	186
I/O	4	P40	P87	N8	190
I/O	4	-	P86	M8	193
I/O, V_{REF}	4	P41	P85	L8	196
I/O	4	-	P84	K8	199
I/O	4	-	P83	N9	202
V_{CCINT}	-	P42	P82	M9	-
GND	-	-	P81	L9	-
I/O	4	P43	P80	K9	205
I/O	4	P44	P79	N10	208
I/O, V_{REF}	4	P45	P77	L10	211
I/O	4	-	P76	N11	214
I/O	4	P46	P75	M11	217
I/O	4	P47	P74	L11	220
GND	-	P48	P73	N12	-
DONE	3	P49	P72	M12	223
V_{CCO}	4	P50	P71	N13	-
V_{CCO}	3	P50	P70	M13	-
$\overline{\text{PROGRAM}}$	-	P51	P69	L12	226
I/O ($\overline{\text{INIT}}$)	3	P52	P68	L13	227
I/O (D7)	3	P53	P67	K10	230
I/O	3	-	P66	K11	233
I/O, V_{REF}	3	P54	P65	K12	236
I/O	3	P55	P63	J10	239
I/O (D6)	3	P56	P62	J11	242

Additional XC2S50 Package Pins *(Continued)*

PQ208

Not Connected Pins					
P55	P56	-	-	-	-

11/02/00

FG256

V_{CCINT} Pins					
C3	C14	D4	D13	E5	E12
M5	M12	N4	N13	P3	P14
V_{CCO} Bank 0 Pins					
E8	F8	-	-	-	-
V_{CCO} Bank 1 Pins					
E9	F9	-	-	-	-
V_{CCO} Bank 2 Pins					
H11	H12	-	-	-	-
V_{CCO} Bank 3 Pins					
J11	J12	-	-	-	-
V_{CCO} Bank 4 Pins					
L9	M9	-	-	-	-
V_{CCO} Bank 5 Pins					
L8	M8	-	-	-	-
V_{CCO} Bank 6 Pins					
J5	J6	-	-	-	-
V_{CCO} Bank 7 Pins					
H5	H6	-	-	-	-
GND Pins					
A1	A16	B2	B15	F6	F7
F10	F11	G6	G7	G8	G9
G10	G11	H7	H8	H9	H10
J7	J8	J9	J10	K6	K7
K8	K9	K10	K11	L6	L7
L10	L11	R2	R15	T1	T16
Not Connected Pins					
P4	R4	-	-	-	-

11/02/00

XC2S100 Device Pinouts

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
GND	-	P143	P1	GND*	GND*	-
TMS	-	P142	P2	D3	D3	-
I/O	7	P141	P3	C2	B1	185
I/O	7	-	-	A2	F5	191
I/O	7	P140	P4	B1	D2	194
I/O	7	-	-	-	E3	197
I/O	7	-	-	E3	G5	200
I/O	7	-	P5	D2	F3	203
GND	-	-	-	GND*	GND*	-
V_{CCO}	7	-	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P139	P6	C1	E2	206

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
I/O	7	-	P7	F3	E1	209
I/O	7	-	-	E2	H5	215
I/O	7	P138	P8	E4	F2	218
I/O	7	-	-	-	F1	221
I/O, V_{REF}	7	P137	P9	D1	H4	224
I/O	7	P136	P10	E1	G1	227
GND	-	P135	P11	GND*	GND*	-
V_{CCO}	7	-	P12	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCINT}	-	-	P13	V_{CCINT}*	V_{CCINT}*	-
I/O	7	P134	P14	F2	H3	230
I/O	7	P133	P15	G3	H2	233
I/O	7	-	-	F1	J5	236
I/O	7	-	P16	F4	J2	239
I/O	7	-	P17	F5	K5	245
I/O	7	-	P18	G2	K1	248
GND	-	-	P19	GND*	GND*	-
I/O, V_{REF}	7	P132	P20	H3	K3	251
I/O	7	P131	P21	G4	K4	254
I/O	7	-	-	H2	L6	257
I/O	7	P130	P22	G5	L1	260
I/O	7	-	P23	H4	L4	266
I/O, IRDY(1)	7	P129	P24	G1	L3	269
GND	-	P128	P25	GND*	GND*	-
V_{CCO}	7	P127	P26	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCO}	6	P127	P26	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
I/O, TRDY(1)	6	P126	P27	J2	M1	272
V_{CCINT}	-	P125	P28	V_{CCINT}*	V_{CCINT}*	-
I/O	6	P124	P29	H1	M3	281
I/O	6	-	-	J4	M4	284
I/O	6	P123	P30	J1	M5	287
I/O, V_{REF}	6	P122	P31	J3	N2	290
GND	-	-	P32	GND*	GND*	-
I/O	6	-	P33	K5	N3	293
I/O	6	-	P34	K2	N4	296
I/O	6	-	P35	K1	P2	302
I/O	6	-	-	K3	P4	305
I/O	6	P121	P36	L1	P3	308
I/O	6	P120	P37	L2	R2	311

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
V_{CCINT}	-	-	P38	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	6	-	P39	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P119	P40	GND*	GND*	-
I/O	6	P118	P41	K4	T1	314
I/O, V_{REF}	6	P117	P42	M1	R4	317
I/O	6	-	-	-	T2	320
I/O	6	P116	P43	L4	U1	323
I/O	6	-	-	M2	R5	326
I/O	6	-	P44	L3	U2	332
I/O, V_{REF}	6	P115	P45	N1	T3	335
V_{CCO}	6	-	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	-	-	GND*	GND*	-
I/O	6	-	P46	P1	T4	338
I/O	6	-	-	L5	W1	341
I/O	6	-	-	-	U4	344
I/O	6	P114	P47	N2	Y1	347
I/O	6	-	-	M4	W2	350
I/O	6	P113	P48	R1	Y2	356
I/O	6	P112	P49	M3	W3	359
M1	-	P111	P50	P2	U5	362
GND	-	P110	P51	GND*	GND*	-
M0	-	P109	P52	N3	AB2	363
V_{CCO}	6	P108	P53	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
V_{CCO}	5	P107	P53	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
M2	-	P106	P54	R3	Y4	364
I/O	5	-	-	N5	V7	374
I/O	5	P103	P57	T2	Y6	377
I/O	5	-	-	-	AA4	380
I/O	5	-	-	P5	W6	383
I/O	5	-	P58	T3	Y7	386
GND	-	-	-	GND*	GND*	-
V_{CCO}	5	-	-	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
I/O, V_{REF}	5	P102	P59	T4	AA5	389
I/O	5	-	P60	M6	AB5	392
I/O	5	-	-	T5	AB6	398
I/O	5	P101	P61	N6	AA7	401
I/O	5	-	-	-	W7	404

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
I/O, V_{REF}	5	P100	P62	R5	W8	407
I/O	5	P99	P63	P6	Y8	410
GND	-	P98	P64	GND*	GND*	-
V_{CCO}	5	-	P65	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
V_{CCINT}	-	P97	P66	V_{CCINT}*	V_{CCINT}*	-
I/O	5	P96	P67	R6	AA8	413
I/O	5	P95	P68	M7	V9	416
I/O	5	-	-	-	AB9	419
I/O	5	-	P69	N7	Y9	422
I/O	5	-	P70	T6	W10	428
I/O	5	-	P71	P7	AB10	431
GND	-	-	P72	GND*	GND*	-
I/O, V_{REF}	5	P94	P73	P8	Y10	434
I/O	5	-	P74	R7	V11	437
I/O	5	-	-	T7	W11	440
I/O	5	P93	P75	T8	AB11	443
V_{CCINT}	-	P92	P76	V_{CCINT}*	V_{CCINT}*	-
I, GCK1	5	P91	P77	R8	Y11	455
V_{CCO}	5	P90	P78	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
V_{CCO}	4	P90	P78	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	P89	P79	GND*	GND*	-
I, GCK0	4	P88	P80	N8	W12	456
I/O	4	P87	P81	N9	U12	460
I/O	4	P86	P82	R9	Y12	466
I/O	4	-	-	N10	AA12	469
I/O	4	-	P83	T9	AB13	472
I/O, V_{REF}	4	P85	P84	P9	AA13	475
GND	-	-	P85	GND*	GND*	-
I/O	4	-	P86	M10	Y13	478
I/O	4	-	P87	R10	V13	481
I/O	4	-	P88	P10	AA14	487
I/O	4	-	-	-	V14	490
I/O	4	P84	P89	T10	AB15	493
I/O	4	P83	P90	R11	AA15	496
V_{CCINT}	-	P82	P91	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	4	-	P92	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	P81	P93	GND*	GND*	-
I/O	4	P80	P94	M11	Y15	499

XC2S150 Device Pinouts

XC2S150 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
GND	-	P1	GND*	GND*	-
TMS	-	P2	D3	D3	-
I/O	7	P3	C2	B1	221
I/O	7	-	-	E4	224
I/O	7	-	-	C1	227
I/O	7	-	A2	F5	230
GND	-	-	GND*	GND*	-
I/O	7	P4	B1	D2	233
I/O	7	-	-	E3	236
I/O	7	-	-	F4	239
I/O	7	-	E3	G5	242
I/O	7	P5	D2	F3	245
GND	-	-	GND*	GND*	-
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P6	C1	E2	248
I/O	7	P7	F3	E1	251
I/O	7	-	-	G4	254
I/O	7	-	-	G3	257
I/O	7	-	E2	H5	260
I/O	7	P8	E4	F2	263
I/O	7	-	-	F1	266
I/O, V_{REF}	7	P9	D1	H4	269
I/O	7	P10	E1	G1	272
GND	-	P11	GND*	GND*	-
V_{CCO}	7	P12	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCINT}	-	P13	V_{CCINT}*	V_{CCINT}*	-
I/O	7	P14	F2	H3	275
I/O	7	P15	G3	H2	278
I/O	7	-	-	H1	284
I/O	7	-	F1	J5	287
I/O	7	P16	F4	J2	290
I/O	7	-	-	J3	293
I/O	7	P17	F5	K5	299
I/O	7	P18	G2	K1	302
GND	-	P19	GND*	GND*	-
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P20	H3	K3	305
I/O	7	P21	G4	K4	308
I/O	7	-	H2	L6	311

XC2S150 Device Pinouts *(Continued)*

XC2S150 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
I/O	7	P22	G5	L1	314
I/O	7	-	-	L5	317
I/O	7	P23	H4	L4	320
I/O, IRDY(1)	7	P24	G1	L3	323
GND	-	P25	GND*	GND*	-
V_{CCO}	7	P26	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCO}	6	P26	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
I/O, TRDY(1)	6	P27	J2	M1	326
V_{CCINT}	-	P28	V_{CCINT}*	V_{CCINT}*	-
I/O	6	-	-	M6	332
I/O	6	P29	H1	M3	335
I/O	6	-	J4	M4	338
I/O	6	P30	J1	M5	341
I/O, V_{REF}	6	P31	J3	N2	344
V_{CCO}	6	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P32	GND*	GND*	-
I/O	6	P33	K5	N3	347
I/O	6	P34	K2	N4	350
I/O	6	-	-	N5	356
I/O	6	P35	K1	P2	359
I/O	6	-	K3	P4	362
I/O	6	-	-	R1	365
I/O	6	P36	L1	P3	371
I/O	6	P37	L2	R2	374
V_{CCINT}	-	P38	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	6	P39	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P40	GND*	GND*	-
I/O	6	P41	K4	T1	377
I/O, V_{REF}	6	P42	M1	R4	380
I/O	6	-	-	T2	383
I/O	6	P43	L4	U1	386
I/O	6	-	M2	R5	389
I/O	6	-	-	V1	392
I/O	6	-	-	T5	395
I/O	6	P44	L3	U2	398
I/O, V_{REF}	6	P45	N1	T3	401
V_{CCO}	6	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	-	GND*	GND*	-

XC2S200 Device Pinouts *(Continued)*

XC2S200 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
GND	-	P198	GND*	GND*	-
I/O	0	P199	A5	B7	188
I/O, V_{REF}	0	P200	C6	E8	191
I/O	0	-	-	D8	197
I/O	0	P201	B5	C7	200
GND	-	-	GND*	GND*	-
I/O	0	-	D6	D7	203
I/O	0	-	-	B6	206
I/O	0	-	-	A5	209
I/O	0	P202	A4	D6	212
I/O, V_{REF}	0	P203	B4	C6	215
V_{CCO}	0	-	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-
GND	-	-	GND*	GND*	-
I/O	0	P204	E6	B5	218
I/O	0	-	D5	E7	221
I/O	0	-	-	A4	224
I/O	0	-	-	E6	230
I/O, V_{REF}	0	P205	A3	B4	233
GND	-	-	GND*	GND*	-
I/O	0	-	C5	A3	236
I/O	0	-	-	B3	239
I/O	0	-	-	D5	242
I/O	0	P206	B3	C5	248
TCK	-	P207	C4	C4	-
V_{CCO}	0	P208	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-
V_{CCO}	7	P208	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-

04/18/01

Notes:
1. IRDY and TRDY can only be accessed when using Xilinx PCI cores.
2. Pads labelled GND*, V_{CCINT}*, V_{CCO} Bank 0*, V_{CCO} Bank 1*, V_{CCO} Bank 2*, V_{CCO} Bank 3*, V_{CCO} Bank 4*, V_{CCO} Bank 5*, V_{CCO} Bank 6*, V_{CCO} Bank 7* are internally bonded to independent ground or power planes within the package.
3. See "VCCO Banks" for details on V_{CCO} banking.

Additional XC2S200 Package Pins

PQ208

Not Connected Pins					
P55	P56	-	-	-	-

11/02/00

FG256

V_{CCINT} Pins					
C3	C14	D4	D13	E5	E12
M5	M12	N4	N13	P3	P14
V_{CCO} Bank 0 Pins					
E8	F8	-	-	-	-
V_{CCO} Bank 1 Pins					
E9	F9	-	-	-	-
V_{CCO} Bank 2 Pins					
H11	H12	-	-	-	-
V_{CCO} Bank 3 Pins					
J11	J12	-	-	-	-
V_{CCO} Bank 4 Pins					
L9	M9	-	-	-	-
V_{CCO} Bank 5 Pins					
L8	M8	-	-	-	-
V_{CCO} Bank 6 Pins					
J5	J6	-	-	-	-
V_{CCO} Bank 7 Pins					
H5	H6	-	-	-	-
GND Pins					
A1	A16	B2	B15	F6	F7
F10	F11	G6	G7	G8	G9
G10	G11	H7	H8	H9	H10
J7	J8	J9	J10	K6	K7
K8	K9	K10	K11	L6	L7
L10	L11	R2	R15	T1	T16
Not Connected Pins					
P4	R4	-	-	-	-